

In the specification

Please replace paragraph [0035] on pages 12-13 of the patent application as filed with the following paragraph:

[0035] FIGS. 3A-3C illustrate a further exemplary embodiment for forming a void 2 in a layer 1 of photo-resist using an exposure step. In FIG. 3A, the photo-resist layer 1 is exposed to radiant energy 7 through a mask 8. The mask has a transmissive portion 81, a partially transmissive portion 83 and a non-transmissive portion 82. The transmissive portion 81 permits radiant energy 7 to expose an exposed portion 12 of the photo-resist 1. The partially transmissive portion [[82]] 83 is partially transparent to the radiant energy, permitting some radiant energy to pass while blocking some radiant energy. The partially transmissive portion [[82]] 83 permits some radiant energy to partially expose a partially exposed portion 17 of the photo-resist 1. The partially exposed portion 17 receives a lower dose than the dose received by the exposed portions 12 received through the transmissive portion 81. The non-transmissive portion 82 blocks radiant energy, leaving an unexposed portion 11 of the photo-resist 1. In an exemplary embodiment using SU8, the transmissivity of the partially transmissive portion 82 is in a range from 5% to 50%. In an exemplary embodiment, the transmissive portion 81 permits radiant energy of a specific wavelength or range of wavelengths to pass. The photo-resist can be selected such that the photo-resist in the first portion will receive a dose sufficient to generate sufficient photo-acid to form the void described herein. The partially transmissive portion permits radiant energy of a different specific wavelength or range of wavelengths to pass. The photo-resist can be selected such that the photo-resist in the second portion will receive a dose sufficient to generate sufficient photo-acid to form the void described herein.